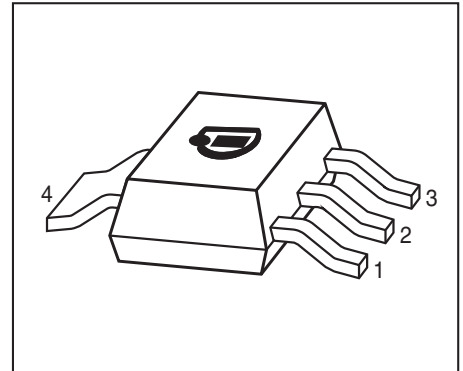


PNP Silicon AF Transistor

- For general AF applications
- High collector current
- High current gain
- Low collector-emitter saturation voltage
- Complementary type: BCP68 (NPN)
- Pb-free (RoHS compliant) package ¹⁾
- Qualified according AEC Q101



Type	Marking	Pin Configuration						Package
		1=B	2=C	3=E	4=C	-	-	
BCP69-25	...-25*	1=B	2=C	3=E	4=C	-	-	SOT223

* Marking is the same than type-name

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CEO}	20	V
Collector-emitter voltage	V_{CES}	25	
Collector-base voltage	V_{CBO}	25	
Emitter-base voltage	V_{EBO}	5	
Collector current	I_C	1	A
Peak collector current, $t_p \leq 10$ ms	I_{CM}	2	
Base current	I_B	100	mA
Peak base current	I_{BM}	200	
Total power dissipation- $T_S \leq 114$ °C	P_{tot}	3	W
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-65 ... 150	

¹⁾Pb-containing package may be available upon special request

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ¹⁾	R_{thJS}	≤ 12	K/W

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

DC Characteristics

Collector-emitter breakdown voltage $I_C = 30\text{ mA}, I_B = 0$	$V_{(BR)CEO}$	20	-	-	V
Collector-base breakdown voltage $I_C = 10\text{ }\mu\text{A}, I_E = 0$	$V_{(BR)CBO}$	25	-	-	
Collector-emitter breakdown voltage $I_C = 10\text{ }\mu\text{A}, V_{BE} = 0$	$V_{(BR)CES}$	25	-	-	
Emitter-base breakdown voltage $I_E = 10\text{ }\mu\text{A}, I_C = 0$	$V_{(BR)EBO}$	5	-	-	
Collector-base cutoff current $V_{CB} = 25\text{ V}, I_E = 0$ $V_{CB} = 25\text{ V}, I_E = 0, T_A = 150\text{ }^\circ\text{C}$	I_{CBO}	-	-	0.1 100	μA
DC current gain ²⁾ $I_C = 5\text{ mA}, V_{CE} = 10\text{ V}$ $I_C = 500\text{ mA}, V_{CE} = 1\text{ V}, \text{BCP69-16}$ $I_C = 500\text{ mA}, V_{CE} = 1\text{ V}, \text{BCP69-25}$ $I_C = 1\text{ A}, V_{CE} = 1\text{ V}$	h_{FE}	50 100 160 60	- 160 250 -	- 250 375 -	-
Collector-emitter saturation voltage ²⁾ $I_C = 1\text{ A}, I_B = 100\text{ mA}$	V_{CEsat}	-	-	0.5	V
Base-emitter voltage ²⁾ $I_C = 5\text{ mA}, V_{CE} = 10\text{ V}$ $I_C = 1\text{ A}, V_{CE} = 1\text{ V}$	$V_{BE(ON)}$	- -	0.6 -	- 1	

AC Characteristics

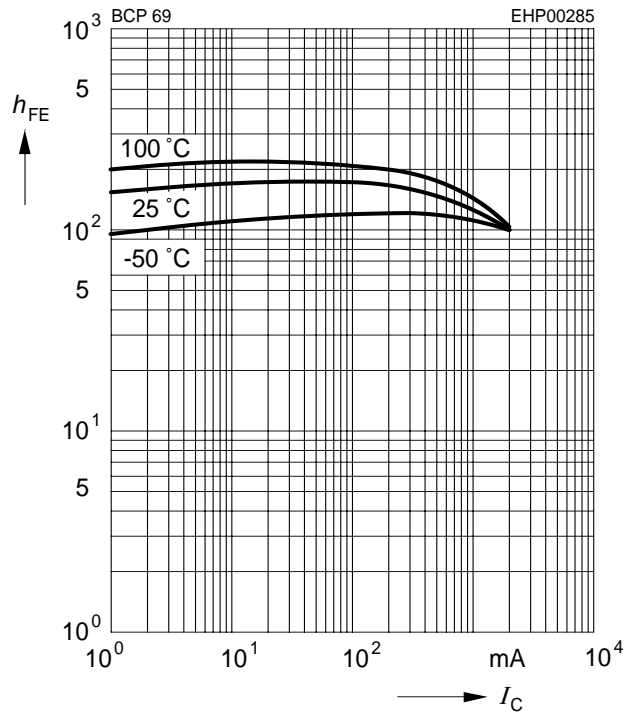
Transition frequency $I_C = 100\text{ mA}, V_{CE} = 5\text{ V}, f = 100\text{ MHz}$	f_T	-	100	-	MHz
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¹⁾For calculation of R_{thJA} please refer to Application Note Thermal Resistance

²⁾Pulse test: $t < 300\mu\text{s}; D < 2\%$

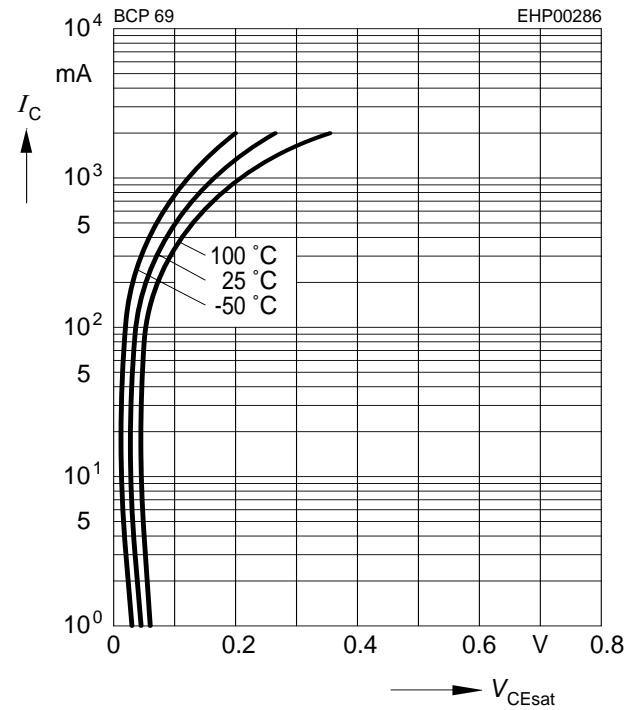
DC current gain $h_{FE} = f(I_C)$

$V_{CE} = 1\text{ V}$



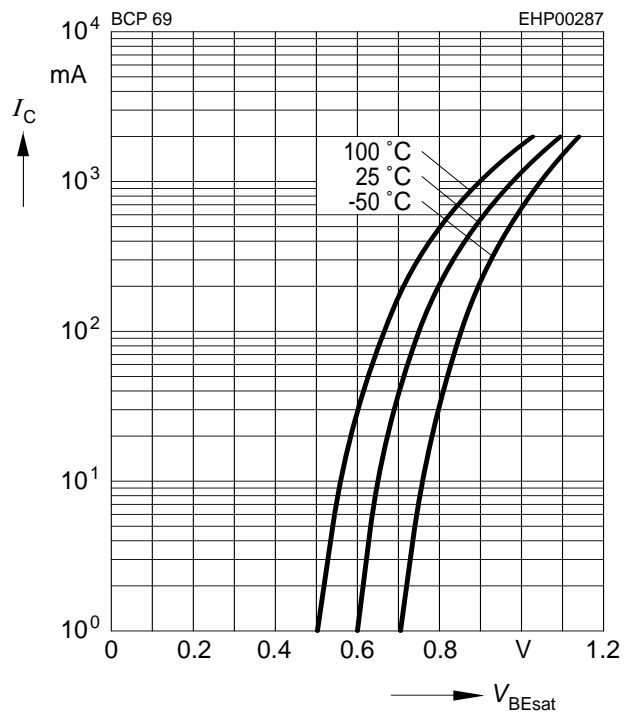
Collector-emitter saturation voltage

$I_C = f(V_{CEsat}), h_{FE} = 10$



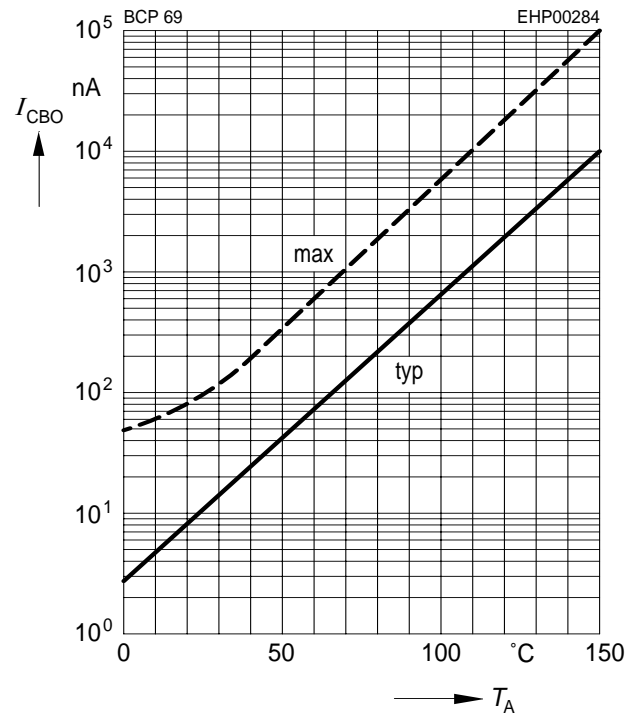
Base-emitter saturation voltage

$I_C = f(V_{BEsat}), h_{FE} = 10$



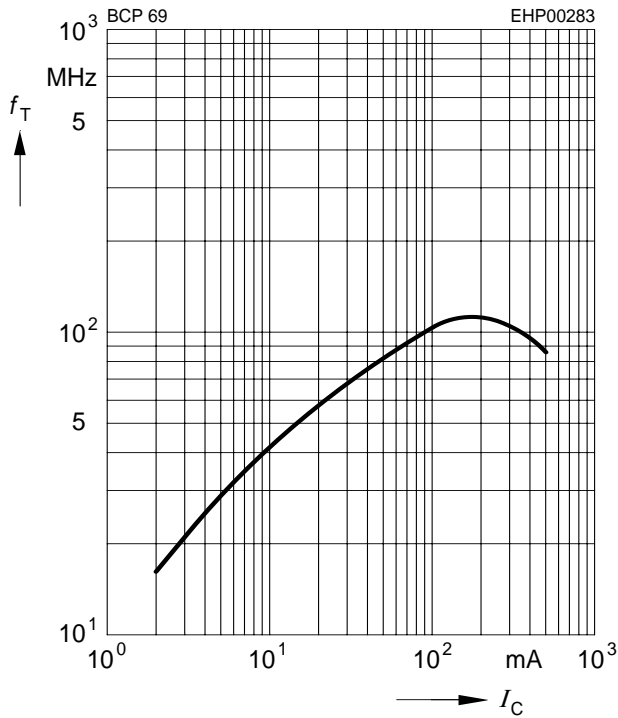
Collector cutoff current $I_{CBO} = f(T_A)$

$V_{CBO} = 25\text{ V}$

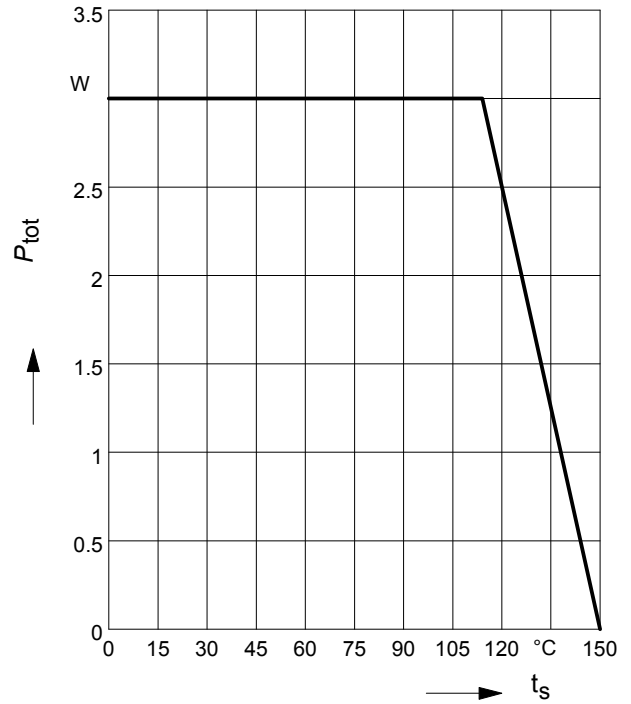


Transition frequency $f_T = f(I_C)$

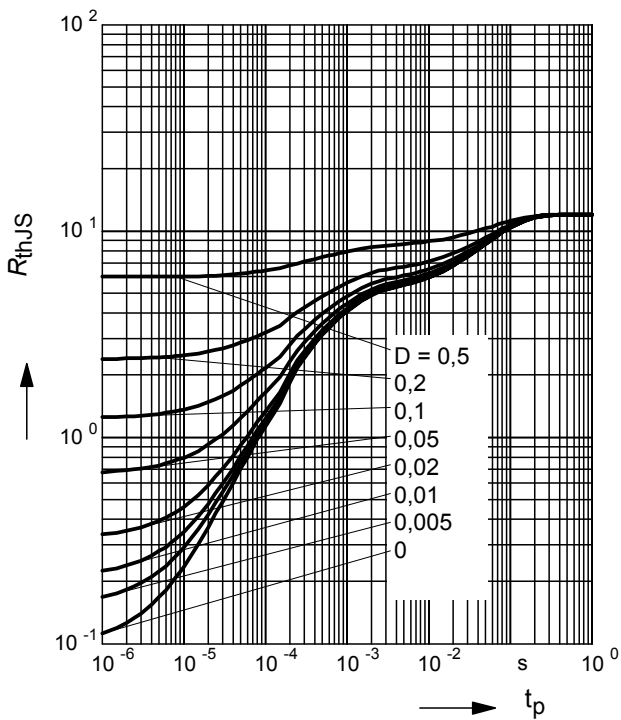
$V_{CE} = 5\text{ V}$



Total power dissipation $P_{tot} = f(T_S)$

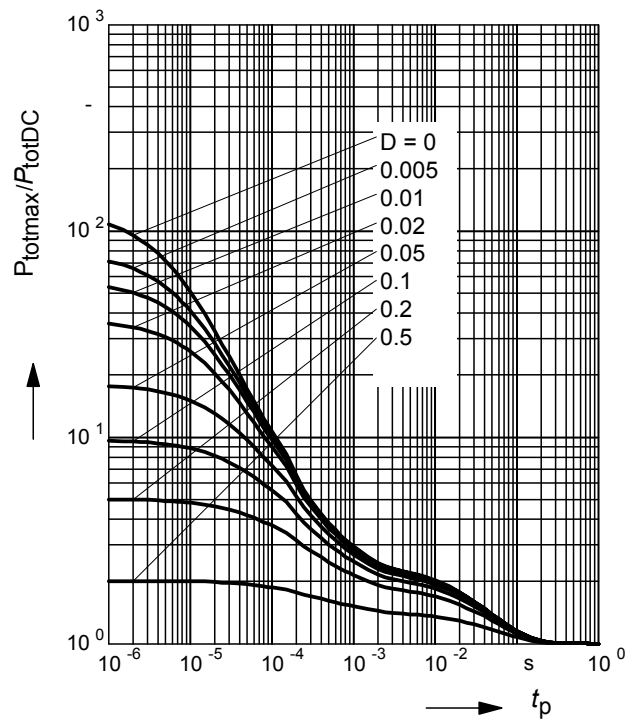


Permissible Pulse Load $R_{thJS} = f(t_p)$

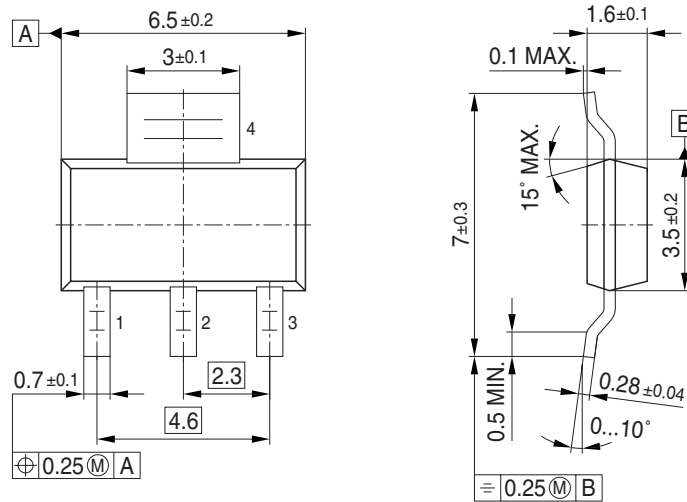


Permissible Pulse Load

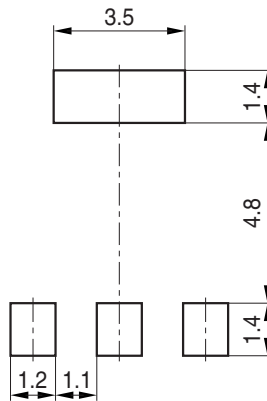
$P_{totmax}/P_{totDC} = f(t_p)$



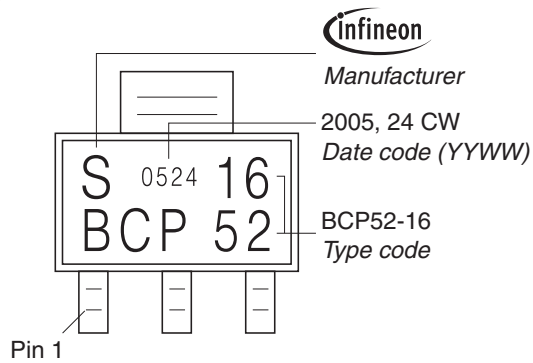
Package Outline



Foot Print

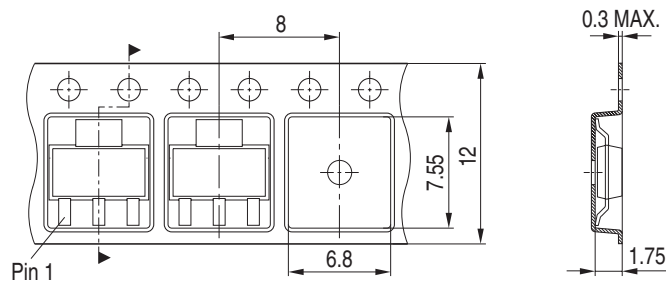


Marking Layout (Example)



Packing

Reel $\varnothing 180 \text{ mm} = 1.000 \text{ Pieces/Reel}$
 Reel $\varnothing 330 \text{ mm} = 4.000 \text{ Pieces/Reel}$



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